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Bipolar resistive switching in $\text{Ba}_{0.5}\text{Sr}_{0.5}\text{Co}_{0.2}\text{Fe}_{0.8}\text{O}_3$ thin films

ZHONGWEN XING, Dept. of Materials Science and Engineering, Nanjing University, NAIJUAN WU, ALEX IGNATIEV, Center for Advanced Materials and Department of Physics, University of Houston — Five-component perovskite $\text{Ba}_{0.5}\text{Sr}_{0.5}\text{Co}_{0.2}\text{Fe}_{0.8}\text{O}_3$ (BSCFO) thin films are reported to have polarized electrical-pulse-induced resistance (EPIR) change at room temperature. Such an EPIR change is attributed to a combined effect of the resistance change of the Schottky barrier and the oxygen ion/vacancy movement near the interface. In the BSCFO, the lower threshold voltage of the electric pulse that leads to nonvolatile resistive changes is close related to its higher oxygen permeability.

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